



MOS TRANSISTOR IN AN INTEGRATED CIRCUIT  
AND ACTIVE AREA FORMING METHOD

ABSTRACT OF THE DISCLOSURE

A method of forming an active area surrounded with an insulating area in a semiconductor substrate, including the steps of forming in the substrate a trench surrounding an active area; filling the trench with an insulating material to form an edge extending beyond the substrate surface at the periphery of the active area; forming a spacer at the periphery of said edge; and implanting a dopant, whereby the implantation in the area located under the spacer is less deep than in the rest of the active area.

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